

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for GSM and GSM EDGE base station applications with frequencies from 865 to 960 MHz. Can be used in Class AB and Class C for all typical cellular base station modulation formats.

- Typical GSM Performance: $V_{DD} = 28$ Volts, $I_{DQ} = 500$ mA, $P_{out} = 72$ Watts CW

Frequency	G_{ps} (dB)	η_D (%)
920 MHz	19.3	51.6
940 MHz	19.3	52.9
960 MHz	19.1	54.1

- Capable of Handling 10:1 VSWR, @ 32 Vdc, 940 MHz, 133 Watts CW Output Power (3 dB Input Overdrive from Rated P_{out})
- Typical P_{out} @ 1 dB Compression Point ≈ 108 Watts CW
- Typical GSM EDGE Performance: $V_{DD} = 28$ Volts, $I_{DQ} = 700$ mA, $P_{out} = 45$ Watts Avg.

Frequency	G_{ps} (dB)	η_D (%)	SR1 @ 400 kHz (dBc)	SR2 @ 600 kHz (dBc)	EVM (% rms)
920 MHz	19.1	43	-64.1	-74.5	1.8
940 MHz	19.1	44	-63.6	-74.6	2.0
960 MHz	19.0	45	-62.8	-75.1	2.3

Features

- Characterized with Series Equivalent Large-Signal Impedance Parameters and Common Source S-Parameters
- Internally Matched for Ease of Use
- Integrated ESD Protection
- Greater Negative Gate-Source Voltage Range for Improved Class C Operation
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

Table 1. Maximum Ratings

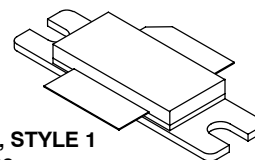
Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +70	Vdc
Gate-Source Voltage	V_{GS}	-6.0, +10	Vdc
Operating Voltage	V_{DD}	32, +0	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature (1,2)	T_J	225	°C

1. Continuous use at maximum temperature will affect MTTF.

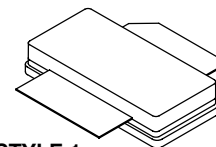
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

MRF8S9100HR3
MRF8S9100HSR3

920-960 MHz, 72 W CW, 28 V
GSM, GSM EDGE
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465-06, STYLE 1
NI-780
MRF8S9100HR3



CASE 465A-06, STYLE 1
NI-780S
MRF8S9100HSR3

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (1,2)	Unit
Thermal Resistance, Junction to Case Case Temperature 80°C, 100 W CW, 28 Vdc, I _{DQ} = 500 mA Case Temperature 81°C, 72 W CW, 28 Vdc, I _{DQ} = 500 mA Case Temperature 82°C, 45 W CW, 28 Vdc, I _{DQ} = 700 mA	R _{θJC}	0.60 0.65 0.69	°C/W

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	2 (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Electrical Characteristics (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

Off Characteristics

Zero Gate Voltage Drain Leakage Current (V _{DS} = 70 Vdc, V _{GS} = 0 Vdc)	I _{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current (V _{DS} = 28 Vdc, V _{GS} = 0 Vdc)	I _{DSS}	—	—	1	μAdc
Gate-Source Leakage Current (V _{GS} = 5 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	—	—	1	μAdc

On Characteristics

Gate Threshold Voltage (V _{DS} = 10 Vdc, I _D = 460 μAdc)	V _{GS(th)}	1.4	2.2	2.9	Vdc
Gate Quiescent Voltage (V _{DD} = 28 Vdc, I _D = 500 mAdc, Measured in Functional Test)	V _{GS(Q)}	2.1	2.9	3.6	Vdc
Drain-Source On-Voltage (V _{GS} = 10 Vdc, I _D = 1.7 Adc)	V _{DS(on)}	0.1	0.17	0.3	Vdc

Functional Tests ⁽³⁾ (In Freescale Test Fixture, 50 ohm system) V_{DD} = 28 Vdc, I_{DQ} = 500 mA, P_{out} = 72 W CW, f = 920 MHz

Power Gain	G _{ps}	18	19.3	23	dB
Drain Efficiency	η _D	50	51.6	—	%
Input Return Loss	IRL	—	-12.4	-9	dB
P _{out} @ 1 dB Compression Point, CW	P1dB	100	—	—	W

Typical Broadband Performance (In Freescale Test Fixture, 50 ohm system) V_{DD} = 28 Vdc, I_{DQ} = 500 mA, P_{out} = 72 W CW

Frequency	G _{ps} (dB)	η _D (%)	IRL (dB)
920 MHz	19.3	51.6	-12.4
940 MHz	19.3	52.9	-14.3
960 MHz	19.1	54.1	-12.2

1. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
2. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.
3. Part internally input matched.

(continued)

Table 4. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
Typical Performances (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 500\text{ mA}$, 920-960 MHz Bandwidth					
P_{out} @ 1 dB Compression Point, CW	P_{1dB}	—	108	—	W
IMD Symmetry @ 100 W PEP, P_{out} where IMD Third Order Intermodulation $\cong 30\text{ dBc}$ (Delta IMD Third Order Intermodulation between Upper and Lower Sidebands $> 2\text{ dB}$)	IMD_{sym}	—	4	—	MHz
VBW Resonance Point (IMD Third Order Intermodulation Inflection Point)	VBW_{res}	—	30	—	MHz
Gain Flatness in 40 MHz Bandwidth @ $P_{out} = 72\text{ W CW}$	G_F	—	0.13	—	dB
Gain Variation over Temperature (-30°C to $+85^\circ\text{C}$)	ΔG	—	0.02	—	dB/ $^\circ\text{C}$
Output Power Variation over Temperature (-30°C to $+85^\circ\text{C}$)	ΔP_{1dB}	—	0.005	—	dB/ $^\circ\text{C}$

Typical GSM EDGE Performances (In Freescale GSM EDGE Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 700\text{ mA}$, $P_{out} = 45\text{ W Avg.}$, 920-960 MHz EDGE Modulation

Frequency	G_{ps} (dB)	η_D (%)	SR1 @ 400 kHz (dBc)	SR2 @ 600 kHz (dBc)	EVM (% rms)
920 MHz	19.1	43	-64.1	-74.5	1.8
940 MHz	19.1	44	-63.6	-74.6	2.0
960 MHz	19.0	45	-62.8	-75.1	2.3

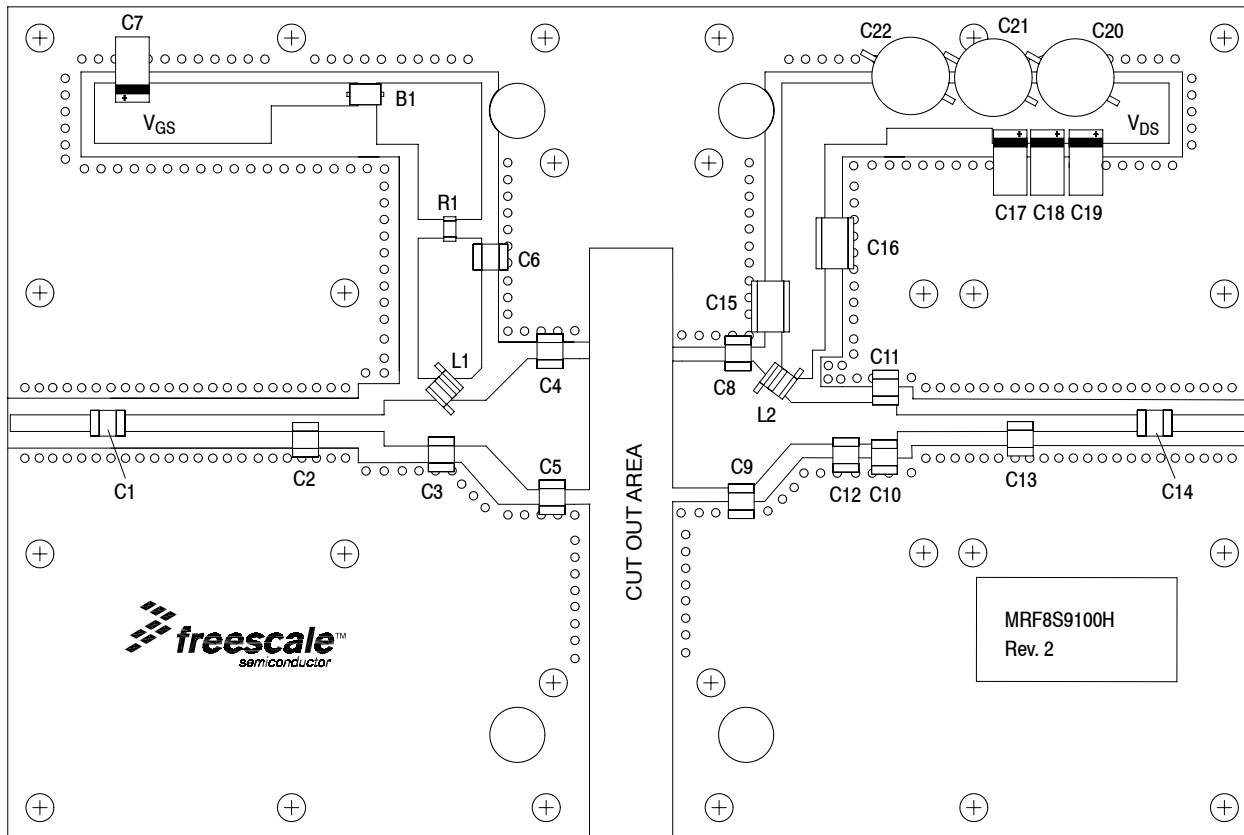


Figure 1. MRF8S9100HR3(HSR3) Test Circuit Component Layout

Table 5. MRF8S9100HR3(HSR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1	Short RF Bead	2743019447	Fair-Rite
C1, C6	47 pF Chip Capacitors	ATC100B470JT500XT	ATC
C2	5.6 pF Chip Capacitor	ATC100B5R6BT500XT	ATC
C3	7.5 pF Chip Capacitor	ATC100B7R5BT500XT	ATC
C4, C5	9.1 pF Chip Capacitors	ATC100B9R1BT500XT	ATC
C7, C17, C18, C19	10 μ F, 35 V Tantalum Capacitors	T491D106K035AT	Kemet
C8, C9	13 pF Chip Capacitors	ATC100B130BT500XT	ATC
C10, C11	2.7 pF Chip Capacitors	ATC100B2R7BT500XT	ATC
C12	6.2 pF Chip Capacitor	ATC100B6R2BT500XT	ATC
C13	1.8 pF Chip Capacitor	ATC100B1R8BT500XT	ATC
C14	20 pF Chip Capacitor	ATC100B200JT500XT	ATC
C15, C16	0.56 μ F, 50 V Chip Capacitors	C1825C564J5RAC-TU	Kemet
C20, C21, C22	470 μ F, 63 V Electrolytic Capacitors	MCGPR63V477M13X26-RH	Multicomp
L1, L2	12.5 nH, 4 Turn Inductors	A04TJLC	Coilcraft
R1	0 Ω , 3 A Chip Resistor	CRCW12060000Z0EA	Vishay
PCB	0.030", $\epsilon_r = 2.55$	AD255A-0300-55-11	Arlon

TYPICAL CHARACTERISTICS

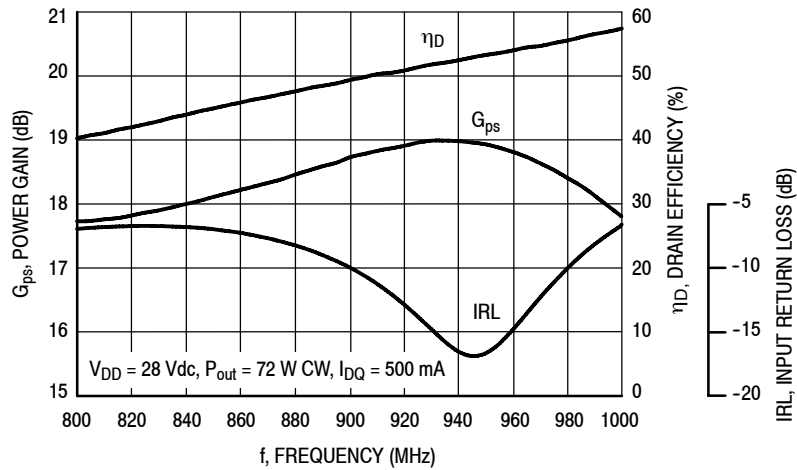


Figure 2. Power Gain, Input Return Loss and Drain Efficiency versus Frequency @ $P_{out} = 72$ Watts CW

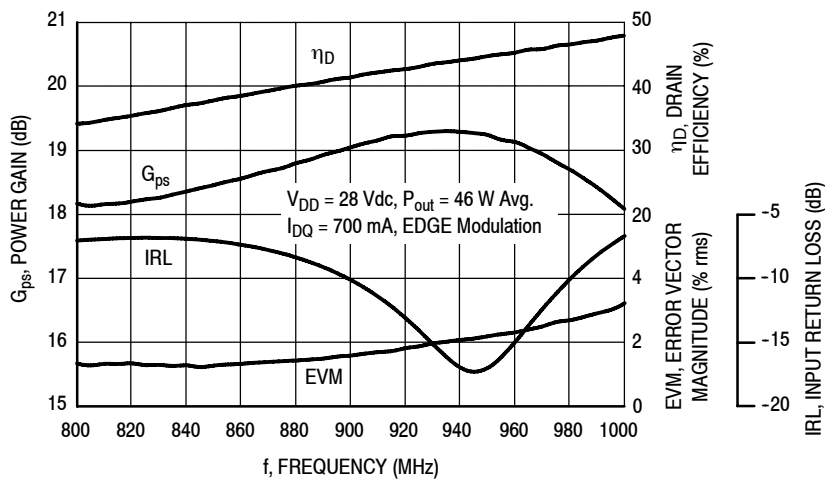


Figure 3. Power Gain, Input Return Loss, EVM and Drain Efficiency versus Frequency @ $P_{out} = 46$ Watts Avg.

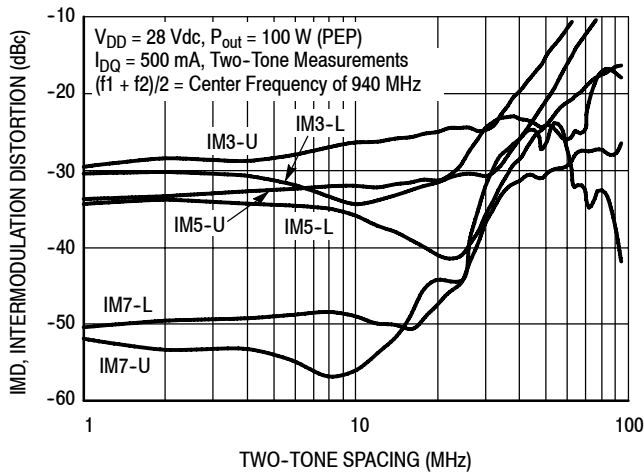


Figure 4. Intermodulation Distortion Products versus Two-Tone Spacing

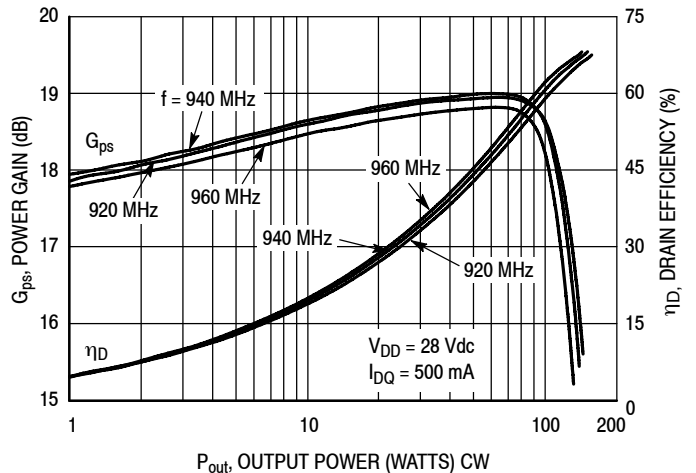


Figure 5. Power Gain and Drain Efficiency versus Output Power

TYPICAL CHARACTERISTICS

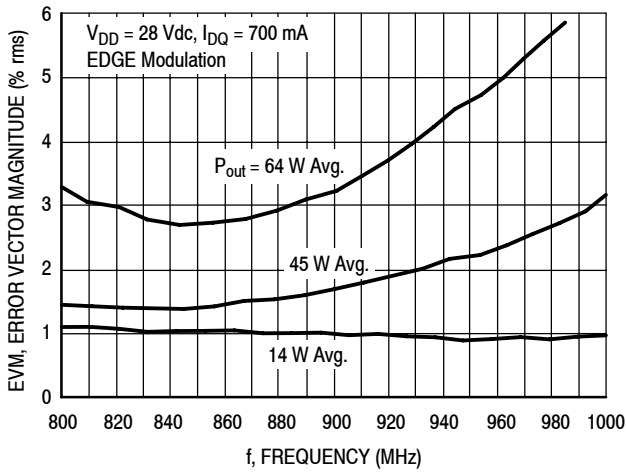


Figure 6. EVM versus Frequency

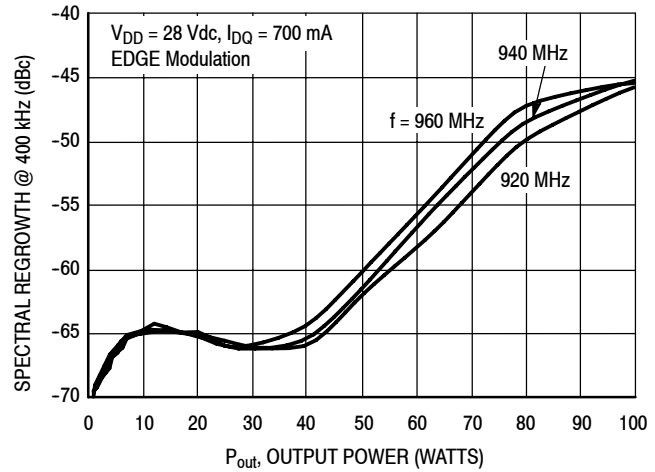


Figure 7. Spectral Regrowth at 400 kHz versus Output Power

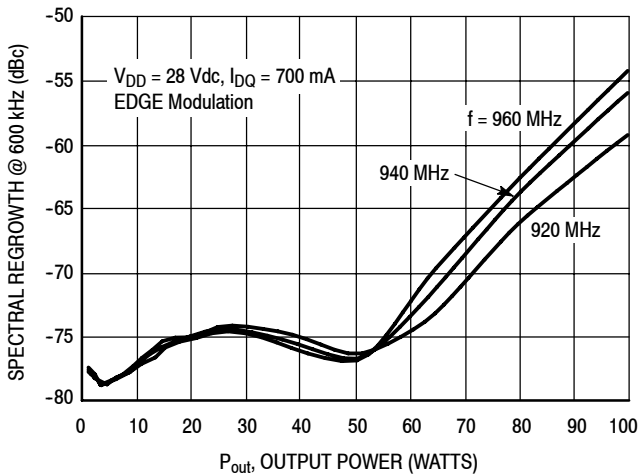


Figure 8. Spectral Regrowth at 600 kHz versus Output Power

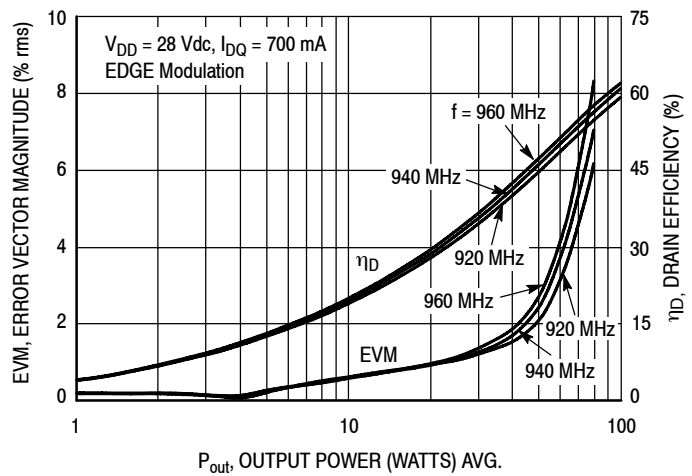


Figure 9. EVM and Drain Efficiency versus Output Power

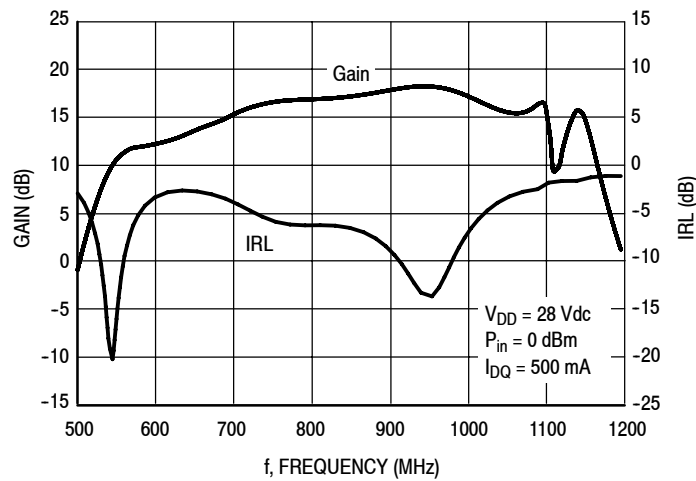


Figure 10. Broadband Frequency Response

GSM TEST SIGNAL

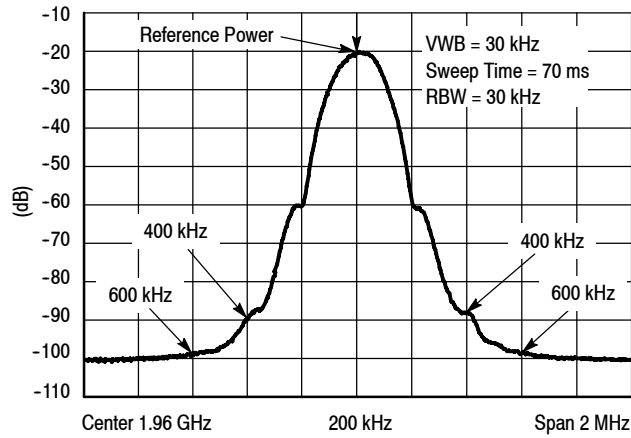


Figure 11. EDGE Spectrum

$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 500 \text{ mA}$, $P_{out} = 72 \text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
820	3.81 - j1.72	1.61 - j0.48
840	3.99 - j1.80	1.62 - j0.34
860	4.13 - j1.97	1.62 - j0.21
880	4.20 - j2.22	1.63 - j0.09
900	4.14 - j2.49	1.62 + j0.02
920	3.96 - j2.74	1.60 + j0.12
940	3.67 - j2.95	1.57 + j0.22
960	3.31 - j3.07	1.53 + j0.32
980	2.91 - j3.09	1.47 + j0.42

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

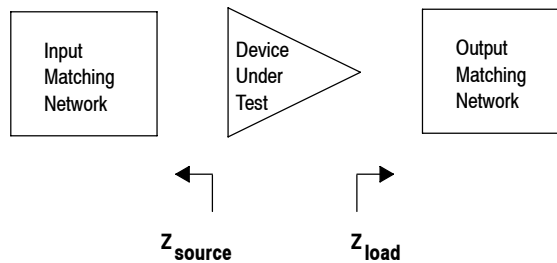
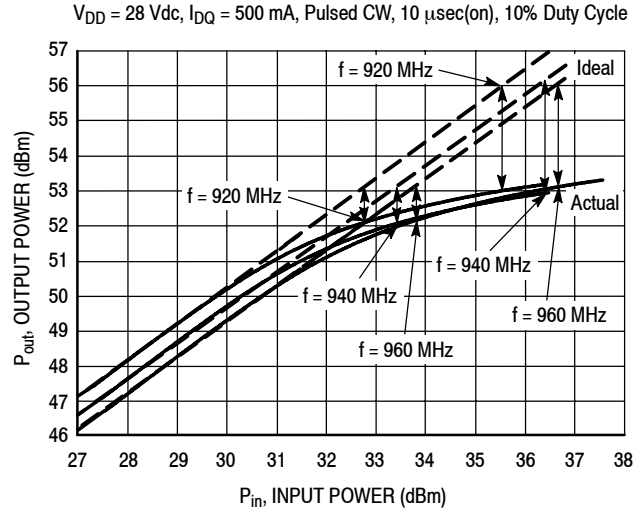


Figure 12. Series Equivalent Source and Load Impedance

ALTERNATIVE PEAK TUNE LOAD PULL CHARACTERISTICS



NOTE: Load Pull Test Fixture Tuned for Peak P1dB Output Power @ 28 V

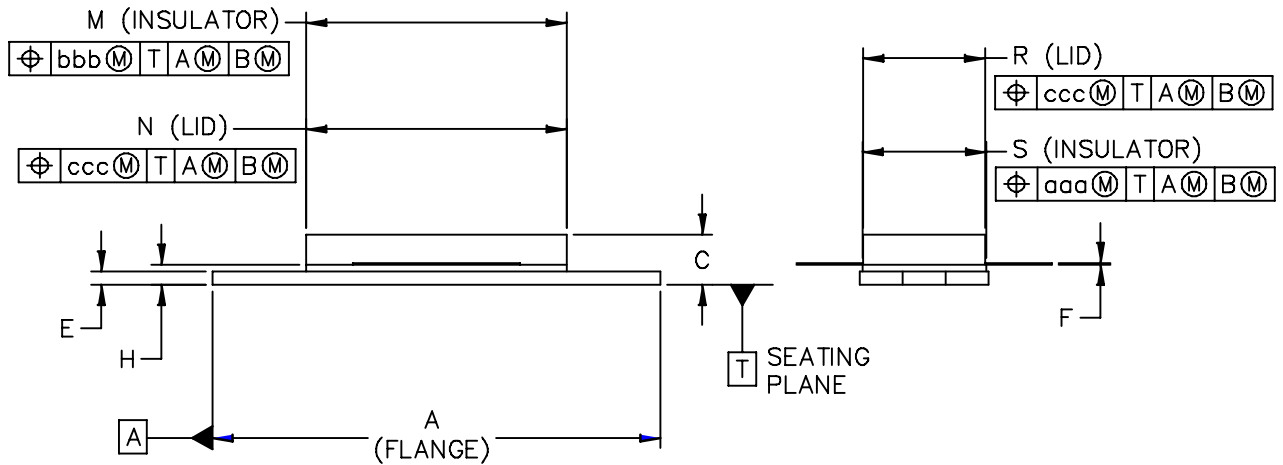
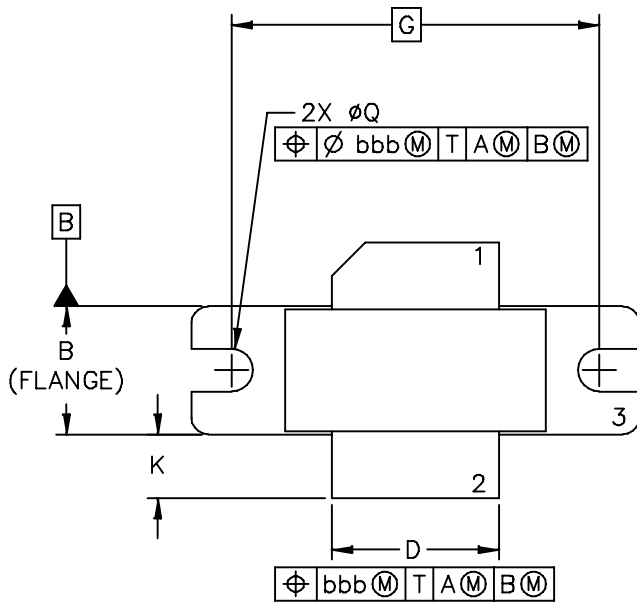
f (MHz)	P1dB		P3dB	
	Watts	dBm	Watts	dBm
920	166	52.2	199	53.0
940	158	52.0	195	52.9
960	166	52.2	209	53.2

Test Impedances per Compression Level

f (MHz)		Z_{source} Ω	Z_{load} Ω
920	P1dB	$3.96 - j2.74$	$1.60 + j0.12$
940	P1dB	$3.67 - j2.95$	$1.57 + j0.22$
960	P1dB	$3.31 - j3.07$	$1.53 + j0.32$

Figure 13. Pulsed CW Output Power versus Input Power @ 28 V

PACKAGE DIMENSIONS



© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED.		MECHANICAL OUTLINE		PRINT VERSION NOT TO SCALE	
TITLE: NI-780		DOCUMENT NO: 98ASB15607C		REV: G	
		CASE NUMBER: 465-06		31 MAR 2005	
		STANDARD: NON-JEDEC			

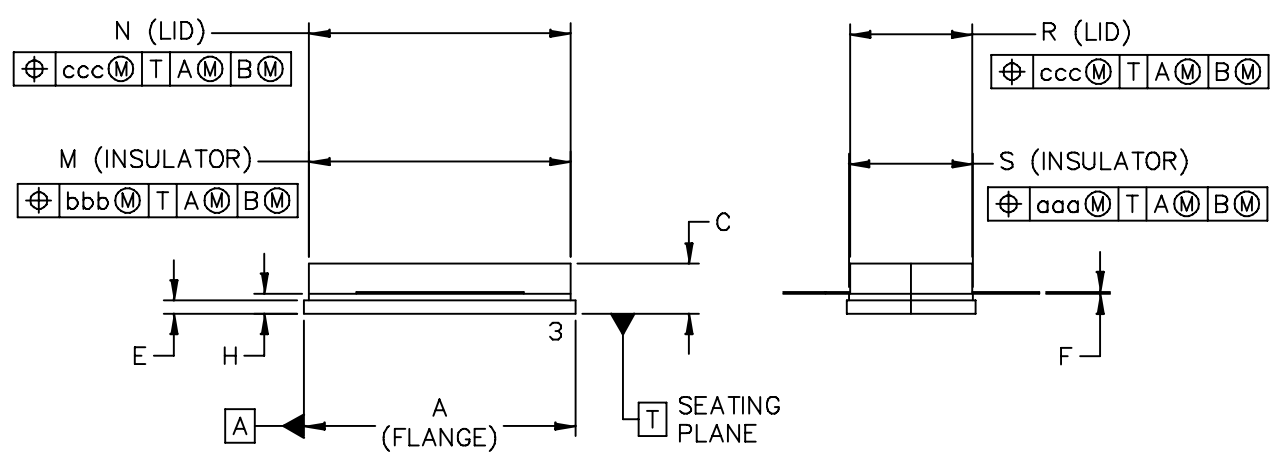
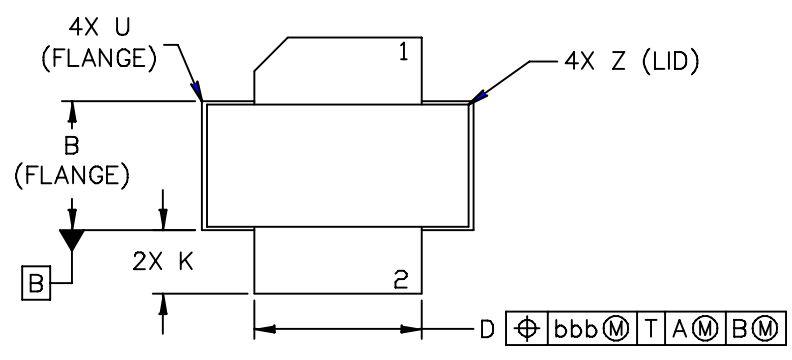
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED .030 (.762) AWAY FROM PACKAGE BODY.

STYLE 1:

- PIN 1. DRAIN
 2. GATE
 3. SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	1.335	– 1.345	33.91	– 34.16	R	.365	– .375	9.27	– 9.53
B	.380	– .390	9.65	– 9.91	S	.365	– .375	9.27	– 9.52
C	.125	– .170	3.18	– 4.32	aaa	– .005	–	–	0.127 –
D	.495	– .505	12.57	– 12.83	bbb	– .010	–	–	0.254 –
E	.035	– .045	0.89	– 1.14	ccc	– .015	–	–	0.381 –
F	.003	– .006	0.08	– 0.15	–	–	–	–	–
G	1.100 BSC		27.94 BSC		–	–	–	–	–
H	.057	– .067	1.45	– 1.7	–	–	–	–	–
K	.170	– .210	4.32	– 5.33	–	–	–	–	–
M	.774	– .786	19.66	– 19.96	–	–	–	–	–
N	.772	– .788	19.6	– 20	–	–	–	–	–
Q	∅.118	– ∅.138	∅3	– ∅3.51	–	–	–	–	–
© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED.			MECHANICAL OUTLINE			PRINT VERSION NOT TO SCALE			
TITLE: NI-780					DOCUMENT NO: 98ASB15607C			REV: G	
					CASE NUMBER: 465-06			31 MAR 2005	
					STANDARD: NON-JEDEC				



© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED.	MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE	
TITLE: NI-780S	DOCUMENT NO: 98ASB16718C	REV: H	
	CASE NUMBER: 465A-06	31 MAR 2005	
	STANDARD: NON-JEDEC		

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M–1994.
2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED .030 (0.762) AWAY FROM PACKAGE BODY.

STYLE 1:

- PIN 1. DRAIN
2. GATE
3. SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	.805	– .815	20.45	– 20.7	U	–	– .040	–	– 1.02
B	.380	– .390	9.65	– 9.91	Z	–	– .030	–	– 0.76
C	.125	– .170	3.18	– 4.32	aaa	–	.005 –	–	0.127 –
D	.495	– .505	12.57	– 12.83	bbb	–	.010 –	–	0.254 –
E	.035	– .045	0.89	– 1.14	ccc	–	.015 –	–	0.381 –
F	.003	– .006	0.08	– 0.15	–	–	– –	–	– –
H	.057	– .067	1.45	– 1.7	–	–	– –	–	– –
K	.170	– .210	4.32	– 5.33	–	–	– –	–	– –
M	.774	– .786	19.61	– 20.02	–	–	– –	–	– –
N	.772	– .788	19.61	– 20.02	–	–	– –	–	– –
R	.365	– .375	9.27	– 9.53	–	–	– –	–	– –
S	.365	– .375	9.27	– 9.52	–	–	– –	–	– –

© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED.		MECHANICAL OUTLINE		PRINT VERSION NOT TO SCALE	
TITLE: NI–780S		DOCUMENT NO: 98ASB16718C		REV: H	
		CASE NUMBER: 465A–06		31 MAR 2005	
		STANDARD: NON–JEDEC			

PRODUCT DOCUMENTATION AND SOFTWARE

Refer to the following documents, tools and software to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

Software

- Electromigration MTTF Calculator
- RF High Power Model
- .s2p File

For Software, do a Part Number search at <http://www.freescale.com>, and select the “Part Number” link. Go to the Software & Tools tab on the part’s Product Summary page to download the respective tool.

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Sept. 2009	• Initial Release of Data Sheet
1	Oct. 2010	• Changed Human Body Model ESD rating from Class 1C to Class 2 to reflect recent ESD test results of the device, p. 2.

How to Reach Us:

Home Page:

www.freescale.com

Web Support:

<http://www.freescale.com/support>

USA/Europe or Locations Not Listed:

Freescale Semiconductor, Inc.
Technical Information Center, EL516
2100 East Elliot Road
Tempe, Arizona 85284
1-800-521-6274 or +1-480-768-2130
www.freescale.com/support

Europe, Middle East, and Africa:

Freescale Halbleiter Deutschland GmbH
Technical Information Center
Schatzbogen 7
81829 Muenchen, Germany
+44 1296 380 456 (English)
+46 8 52200080 (English)
+49 89 92103 559 (German)
+33 1 69 35 48 48 (French)
www.freescale.com/support

Japan:

Freescale Semiconductor Japan Ltd.
Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku,
Tokyo 153-0064
Japan
0120 191014 or +81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:

Freescale Semiconductor China Ltd.
Exchange Building 23F
No. 118 Jianguo Road
Chaoyang District
Beijing 100022
China
+86 10 5879 8000
support.asia@freescale.com

For Literature Requests Only:

Freescale Semiconductor Literature Distribution Center
1-800-441-2447 or +1-303-675-2140
Fax: +1-303-675-2150
LDCForFreescaleSemiconductor@hibbertgroup.com

Information in this document is provided solely to enable system and software implementers to use Freescale Semiconductor products. There are no express or implied copyright licenses granted hereunder to design or fabricate any integrated circuits or integrated circuits based on the information in this document.

Freescale Semiconductor reserves the right to make changes without further notice to any products herein. Freescale Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Freescale Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters that may be provided in Freescale Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals", must be validated for each customer application by customer's technical experts. Freescale Semiconductor does not convey any license under its patent rights nor the rights of others. Freescale Semiconductor products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Freescale Semiconductor product could create a situation where personal injury or death may occur. Should Buyer purchase or use Freescale Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold Freescale Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Freescale Semiconductor was negligent regarding the design or manufacture of the part.

Freescale™ and the Freescale logo are trademarks of Freescale Semiconductor, Inc. All other product or service names are the property of their respective owners.

© Freescale Semiconductor, Inc. 2009-2010. All rights reserved.